Gap opening in the zeroth Landau level of graphene

A. J. M. Giesbers,1 L. A. Ponomarenko,2 K. S. Novoselov,2
A. K. Geim,2 M. I. Katsnelson,3 J. C. Maan,1 and U. Zeitler1,*

1 High Field Magnet Laboratory, Institute for Molecules and Materials,
Radboud University Nijmegen, Toernooiveld 7, 6525 ED Nijmegen, The Netherlands
2 Department of Physics, University of Manchester, M13 9FL, Manchester, UK
3 Theory of Condensed Matter, Institute for Molecules and Materials,
Radboud University Nijmegen, Heyendaalseweg 135, 6525 AJ Nijmegen The Netherlands

(Dated: April 6, 2009)

We have measured a strong increase of the low-temperature resistivity $\rho_{xx}$ and a zero-value plateau in the Hall conductivity $\sigma_{xy}$ at the charge neutrality point in graphene subjected to high magnetic fields up to 30 T. We explain our results by a simple model involving a field dependent splitting of the lowest Landau level of the order of a few Kelvin, as extracted from activated transport measurements. The model reproduces both the increase in $\rho_{xx}$ and the anomalous $\nu = 0$ plateau in $\sigma_{xy}$ in terms of coexisting electrons and holes in the same spin-split zero-energy Landau level.

PACS numbers: 73.43.-f, 73.63.-b, 71.70.Di

In a magnetic field, graphene displays an unconventional Landau-level spectrum of massless chiral Dirac fermions [1, 2, 3, 4]. In particular, a Landau level shared equally between electrons and holes of opposite chirality exists at zero-energy around the charge neutrality point (CNP). Due to the coexistence of carriers with opposite charge, graphene behaves as a compensated semimetal at the CNP with a finite resistivity $\rho_{xx}$ and a zero Hall resistivity $\rho_{xy}$.

Recently, the nature of the CNP in high magnetic fields has attracted considerable theoretical interest (see Ref. [5] and references therein). Experimentally, in the metallic regime, the transport behavior around the CNP can be explained using counter-propagating edge channels [6]. On the other hand, the high-field resistivity at the CNP was shown to diverge strongly, an effect recently analyzed in terms of coexisting electrons and holes in the same spin-split zero-energy Landau level.

The monolayer graphene devices (see top left inset Fig. 1a) are deposited on Si/SiO$_2$ substrate using methods as already reported elsewhere [10, 11]. The doped Si acts as a back-gate and allows to adjust the charge-carrier concentration in the graphene film from highly hole-doped to highly electron-doped. Prior to the experiments the devices were annealed at 390 K during several hours removing most of the surface impurities [12] and increasing the low-temperature mobility from $\mu = 0.47$ m$^2$(Vs)$^{-1}$ to $\mu = 1.0$ m$^2$(Vs)$^{-1}$. All measurements were performed with standard AC-techniques at low enough currents to avoid any heating effects.

Charge carriers in graphene behave as massless chiral Dirac fermions with a constant velocity $c \approx 10^6$ m/s and thus a linear dispersion $E = \pm c |k|$ [1, 2, 13]. The $\pm$ sign refers to electrons with positive energies and holes with negative energies, respectively. In a magnetic field, this linear spectrum splits up into non-equidistant Landau levels at $E_N = \pm c v F h B N$ [4]. Higher Landau levels ($N \geq 1$) are fourfold degenerate and filled with either electrons ($E > 0$) or holes ($E < 0$). The zeroth Landau level ($N = 0$) is half filled with electrons and half filled with holes of opposite chirality.

A consequence of this peculiar Landau-level structure is the half-integer quantum Hall effect [1, 2]. Figure 1a and b visualize this effect by means of magneto-transport experiments in a graphene field-effect transistor (FET) at $B = 30$ T. At large negative back-gate voltages ($V_g < -40$ V) two hole levels are completely filled, the Hall resistivity is quantized to $\rho_{xy} = \hbar/6e^2 = 4.3$ k$\Omega$ and the longitudinal resistivity $\rho_{xx}$ develops a zero-minimum. Moving $V_g$ toward zero depopulates the $N = 1$ hole level and moves the Hall resistance to the following plateau, $\rho_{xy} = \hbar/4e^2 = 12.9$ k$\Omega$ accompanied by another zero
FIG. 1: (color online) (a) $\rho_{xy}$ as a function of back-gate voltage $V_G$ (top $x$-axis) and charge carrier concentration $n$ (bottom $x$-axis) measured between contacts 3 and 5 as shown in the scanning electron micrograph in the top left inset at a fixed magnetic field $B = 30$ T. (b) $\rho_{xx}$ at $B = 30$ T measured at the same temperatures as in (a). Note the $x$-axis break and the 20-times magnification for high electron/hole concentrations. The left inset in (b) shows the temperature dependence of $\rho_{xx}$ at the charge CNP for different $B$. The right inset displays the magnetic field dependence of $\rho_{xx}$ at the CNP for different $T$.

In the following we will concentrate on the electronic behavior of graphene around the CNP in high magnetic fields and at low temperatures. Our experimental findings are summarized in Figure 1c. For high magnetic fields ($B > 20$ T) $\rho_{xx}$ strongly increases from a few tens of kilo-ohms to several mega-ohms when the temperatures is lowered down to 0.4 K (left inset in Fig. 1c). Such a field-induced transition can also be seen in the right inset in Fig. 1c: Whereas the magnetoresistance displays a moderate field dependence for sufficiently high temperatures, it starts to increase strongly for $B > 20$ T for the lowest temperature $T = 0.4$ K.

At zero magnetic field the resistivity at the CNP behaves as can be expected, it increases with decreasing temperature toward $h/4e^2$, as carriers are slightly frozen out.

To gain more insight into the peculiar behavior at the CNP we have calculated the longitudinal conductivity $\sigma_{xx}$ and Hall conductivity $\sigma_{xy}$ from the experimentally measured $\rho_{xx}$ and $\rho_{xy}$ by tensor inversion. Possible artifacts due to admixtures of $\rho_{xx}$ on $\rho_{xy}$ and vice versa, caused by contact misalignment and inhomogeneities, were removed, by symmetrizing all measured resistances for positive and negative magnetic fields.

Fig. 2a shows the two components of the conductivity tensor at $B = 30$ T. At low temperatures, the Hall conductivity $\sigma_{xy}$ develops an additional, clearly pronounced, zero-value quantum Hall plateau around the CNP and the longitudinal conductivity $\sigma_{xx}$ displays a thermally activated minimum. Both features are an immediate consequence of the strongly increasing $\rho_{xx}$ at the CNP.

Both the minimum in $\sigma_{xx}$ and the zero-value plateau in $\sigma_{xy}$ at the CNP disappear at elevated temperatures (Fig. 2a) pointing toward an activated transport behavior. Indeed, when plotting $\sigma_{xx}$ in an Arrhenius plot...
We can relate the observed activated behavior to the opening of a gap in the zeroth Landau level (inset in Fig. 2a), \( \Delta = 2\Delta_a \), and, therefore, to a partial lifting of its four-fold degeneracy. The experimentally determined field dependence of this gap is shown in Fig. 2c. The gap only becomes visible for fields above 15 T because of a finite width \( \Gamma_0 \) of the split Landau level at zero energy; linear extrapolation of the experimental data to zero field yields \( \Gamma_0 \approx 30 \text{ K} \). The linear variation of \( \Delta \) with magnetic field suggests that the splitting might be spin related. For comparison we have plotted the theoretical Zeeman splitting \( \Delta_Z = g\mu_B B \) for a spin-split zeroth Landau level, with a free-electron \( g \)-factor \( g = 2 \) [8] (\( \mu_B \) the Bohr magneton). The slightly higher slope of the experimentally measured gap may be explained by a sharpening of the zeroth Landau level (i.e. a reduction of \( \Gamma_0 \)) with increasing field [16], or, alternatively by a slight exchange enhancement of the splitting.

The consequences of the opening of a gap can be understood intuitively using a simple model (Fig. 3): The density of states of graphene in a magnetic field consist of a series of Landau levels occupied by electrons or holes. Each Landau level is represented by a Gaussian with a degeneracy of holes. Each Landau level is represented by a Gaussian.

![Figure 3](image.png)

**FIG. 3.** (a) Schematic illustration of the density of states for electrons (red) and holes (blue) in graphene in a magnetic field without spin-splitting (top) and including spin splitting (bottom). The width of the higher Landau levels is in reality much larger than illustrated (see text). (b) \( \sigma_{xx} \) and \( \sigma_{xy} \) as a function of charge carrier concentration for unsplit (dotted lines) and split (solid line) Landau levels calculated for \( B = 30 \text{ T} \) and \( T = 1 \text{ K} \) and using \( g = 2 \).

An additional spin-splitting of all the Landau levels is schematically introduced into the model in the lower part of Fig. 3a. The splitting is only resolved in the lowest Landau level, where the level width is already small enough (20 K). Due to the large broadening of the higher levels (400 K [16]) it remains unresolved here. Fig. 3b shows how this splitting nicely reproduces the plateau in \( \sigma_{xy} \) accompanied by a minimum in \( \sigma_{xx} \). As soon as the splitting exceeds the width of the extended states in the lowest Landau level, the resistivity \( \rho_{xx} \) at the CNP starts to increase as a natural consequence of the tensor inversion of the developing minimum in \( \sigma_{xx} \) and the quantized Hall plateau in \( \sigma_{xy} \).

The proposed density of states in Fig. 3b. not only explains the experimentally observed increase in \( \rho_{xx} \) at the CNP but also the behavior of \( \rho_{xy} \). In conventional semiconductors with a gap, \( \rho_{xy} \) develops a singularity around the CNP when either electrons or holes are fully depleted. In our graphene samples, however, \( \rho_{xy} \) is moving through zero from the \( v = -2 \) plateau with \( \rho_{xy} = -h/2e^2 = 12.9 \text{ k}\Omega \) to the \( v = +2 \) plateau at \( h/2e^2 \). This observation implies that electrons and holes are coexisting both below and above the CNP and graphene behaves as a compensated semimetal with as many hole states as electron states occupied at the CNP.

It should be mentioned in this context that Zhang et al. have observed an additional splitting of the lowest Landau level in other samples [8, 9] resulting into additional

\[
\sigma_{xx} \propto \exp \left( -\frac{\Delta_a}{kT} \right),
\]
quantum Hall plateaus at $\rho_{xy} = \pm \hbar/e^2 = \pm 25.8$ kΩ and $\nu = \pm 1$ minima in $\rho_{xx}$. To explain these results, the degeneracy of electron and hole states has to be removed by lifting the sublattice degeneracy. In this respect, the absence of $\nu = \pm 1$ state in our and other experiments [6, 7, 16] points to a larger disorder, confirmed by the lower mobility, which prevents symmetry breaking. Therefore, we deal with a symmetric density of states for electrons and holes with two-fold degenerate spin-split levels shared by electrons and holes simultaneously.

An important consequence of our experiments is that the gaps measured are more than an order of magnitude smaller than interaction induced gaps. Indeed, the characteristic energy of electron-electron correlation $I = e^2/4\pi\epsilon_0\epsilon_r l_B$ (where $l_B = \sqrt{\hbar/eB}$ is the magnetic length and $\epsilon_r \approx 2.5$ is the effective dielectric constant for graphene on silicon dioxide) amounts to about 1400 K at 30 T and exceeds the width of the zero-energy Landau level $\Gamma_0$ by nearly two orders of magnitude. According to a simple Stoner-like theory of quantum Hall ferromagnetism [23] this should result in spontaneous breaking of spin and, possibly, valley degeneracy with the formation of quantum Hall ferromagnetism. Since we do not see any evidences of the spontaneous breaking, the effective Stoner parameter is apparently reduced to the value of order of $\Gamma_0$. Probably the sample mobility is not high enough for the stable appearance of a ferromagnetic phase as proposed in Fig. 1 of Ref. 23. A suppression of the Stoner parameter is also what one would naturally expect for narrow-band itinerant-electron ferromagnets due to so called $T$-matrix renormalization [24, 25]. Unfortunately, for the case of quantum-Hall ferromagnetism a consequent theoretical treatment of the effective Stoner criterion with a controllable small parameter is only possible for the limit of high Landau levels [26, 27] and, admittedly, numerous other theoretical scenarios may be considered (see e.g. Ref. 5 and references therein). Therefore, further theoretical efforts are certainly required to clarify this issue.

In conclusion, we have measured the transport properties of the zeroth Landau level in graphene at low temperatures and high magnetic fields. An increasing longitudinal resistance accompanied by a zero crossing in the Hall resistivity at the CNP leads to a flat plateau in the Hall conductivity together with a thermally activated minimum in the longitudinal conductivity. This behavior can be related to the opening of a Zeeman-gap in the density of states of the zeroth Landau level, which reasonably reproduces the features observed experimentally.

This work is part of the research program of the ‘Stichting voor Fundamenteel Onderzoek der Materie (FOM)’, which is financially supported by the ‘Nederlandse Organisatie voor Wetenschappelijk Onderzoek (NWO)’. It has been supported by EuroMagNET under EU contract RII3-CT-2004-506239, the EPSRC, the Royal Society and the European Research Council (Program ‘Ideas’, Call: ERC-2007-StG).

* U.Zeitler@science.ru.nl